

OP196/OP296/OP496

FEATURES

- Rail-to-Rail Input and Output Swing
- Low Power: 60 μ A/Amplifier
- Gain Bandwidth Product: 450 kHz
- Single-Supply Operation: +3 V to +12 V
- Low Offset Voltage: 300 μ V max
- High Open-Loop Gain: 500 V/mV
- Unity-Gain Stable
- No Phase Reversal

APPLICATIONS

- Battery Monitoring
- Sensor Conditioners
- Portable Power Supply Control
- Portable Instrumentation

GENERAL DESCRIPTION

The OP196 family of CBCMOS operational amplifiers features micropower operation and rail-to-rail input and output ranges.

The extremely low power requirements and guaranteed operation from +3 V to +12 V make these amplifiers perfectly suited to monitor battery usage and to control battery charging. Their dynamic performance, including 26 nV/ $\sqrt{\text{Hz}}$ voltage noise density, recommends them for battery-powered audio applications. Capacitive loads to 200 pF are handled without oscillation.

The OP196/OP296/OP496 are specified over the HOT extended industrial (-40°C to +125°C) temperature range. +3 V operation is specified over the 0°C to +125°C temperature range.

The single OP196 and the dual OP296 are available in 8-pin plastic DIP and SO-8 surface mount packages. The quad OP496 is available in 14-pin plastic DIP and narrow SO-14 surface mount packages. Check factory for availability of the OP296 and OP496 in TSSOP packages.

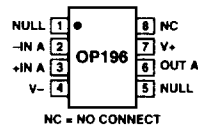
ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option*
OP196GP	-40°C to +125°C	8-Pin Plastic DIP	N-8
OP196GS	-40°C to +125°C	8-Pin SOIC	SO-8
OP296GP	-40°C to +125°C	8-Pin Plastic DIP	N-8
OP296GS	-40°C to +125°C	8-Pin SOIC	SO-8
OP296HRU	-40°C to +125°C	8-Pin TSSOP	RU-8
OP296GBC	+25°C	DICE	
OP496GP	-40°C to +125°C	14-Pin Plastic DIP	N-14
OP496GS	-40°C to +125°C	14-Pin SOIC	SO-14
OP496HRU	-40°C to +125°C	14-Pin TSSOP	RU-14
OP496GBC	+25°C	DICE	

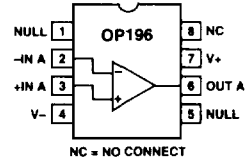
*For outline information see Package Information section.

PIN CONFIGURATIONS

8-Lead Narrow-Body SO (S Suffix)



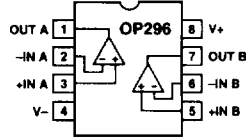
8-Lead Epoxy DIP (P Suffix)



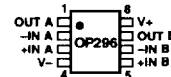
8-Lead Narrow-Body SO (S Suffix)



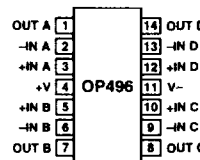
8-Lead Epoxy DIP (P Suffix)



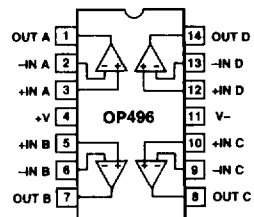
8-Lead TSSOP (RU Suffix)



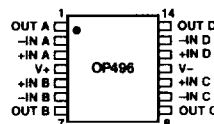
14-Lead Narrow-Body SO (S Suffix)



14-Lead Epoxy DIP (P Suffix)



14-Lead TSSOP (RU Suffix)



OP196/OP296/OP496—SPECIFICATIONS

ELECTRICAL SPECIFICATIONS (@ $V_S = +5.0\text{ V}$, $V_{CM} = +2.5\text{ V}$, $T_A = +25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	OP196G, OP296G, OP496G $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		35	300	μV
		OP296H, OP496H $40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			650	μV
					800	μV
Input Bias Current	I_B	$40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		± 10	± 35	nA
Input Offset Current	I_{OS}	$40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		± 1.5	± 5	nA
Input Voltage Range	V_{CM}		0		+5.0	V
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 5.0\text{ V}$, $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	65			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 100\text{ k}\Omega$, $0.30\text{ V} \leq V_{OUT} \leq 4.7\text{ V}$, $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	150	200		V/mV
Long-Term Offset Voltage	V_{OS}	G Grade, Note 1			550	μV
		H Grade, Note 1			1	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	G Grade, Note 2		1.5		$\mu\text{V}/^\circ\text{C}$
		H Grade, Note 2		2		$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage Swing High	V_{OH}	$I_L = 100\text{ }\mu\text{A}$	4.85	4.92		V
		$I_L = 1\text{ mA}$	4.30	4.56		V
Output Voltage Swing Low	V_{OL}	$I_L = 2\text{ mA}$		4.1		V
		$I_L = 100\text{ }\mu\text{A}$		36	70	mV
		$I_L = 1\text{ mA}$		350	450	mV
Output Current	I_{OUT}	$I_L = 2\text{ mA}$		750		mV
				± 4		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$\pm 2.5\text{ V} \leq V_S \leq \pm 6\text{ V}$, $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	85			dB
Supply Current per Amplifier	I_{SY}	$V_{OUT} = 2.5\text{ V}$, $R_L = \infty$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		45	60 80	μA μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100\text{ k}\Omega$		0.3		V/ μs
Gain Bandwidth Product	GBP			350		kHz
Phase Margin	θ_m			47		Degrees
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz		0.8		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		26		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		0.19		$\text{pA}/\sqrt{\text{Hz}}$

NOTES

¹Long-term offset voltage is guaranteed by a 1000 hour life test performed on three independent lots at $+125^\circ\text{C}$, with an LTPD of 1.3.

²Offset voltage drift is the average of the -40°C to $+25^\circ\text{C}$ delta and the $+25^\circ\text{C}$ to $+125^\circ\text{C}$ delta.

Specifications subject to change without notice.